

N-channel SiC power MOSFET

V _{DSS}	750V
$R_{DS(on)}$ (Typ.)	26mΩ
I _D *1	56A
P_D	176W

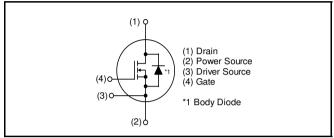
Outline



Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Application

- Solar inverters
- DC/DC converters
- · Switch mode power supplies
- · Induction heating
- Motor drives

Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT4026DR

● **Absolute maximum ratings** (T_{vj} = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	750	V	
Continuous drain	V V	$T_c = 25^{\circ}C$, , *1	56	Α
and source current	$V_{GS} = V_{GS_on}$	T _c = 100°C	l _D , l _S *1	39	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	$T_c = 25^{\circ}C$	I _{D,pulse} *2	91	Α
Body diode pulsed forward	ard current	T _c = 25°C	I _{S,pulse} *1,*3	56	Α
Body diode surge forward current		$V_{GS} = 0 V$	I _{S,pulse} *1,*4	91	Α
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V	
Gate - source surge voltage (t _{surge} < 300ns)		$V_{\rm GSS_surge}^{*5}$	-4 to +23	V	
Recommended turn-on gate - source drive voltage		ive voltage	${\sf V_{GS_on}}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V	
Virtual junction temperature		T_{vj}	175	°C	
Range of storage temperature		T_{stg}	-40 to +175	°C	

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol Conditions -		Values			Unit
r didilletei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V	$V_{GS} = 0 \text{ V}, I_D = 9.2 \text{mA}$				V
	V (BR)DSS	$T_{vj} = 25^{\circ}C$	750	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam carrott		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V$, $V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	5.55	$V_{GS} = -4V$, $V_{DS} = 0V$	ı	ı	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 15.4mA$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 29A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	26	34	mΩ
S. State I State		T _{vj} = 150°C	-	44	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	1	-	Ω

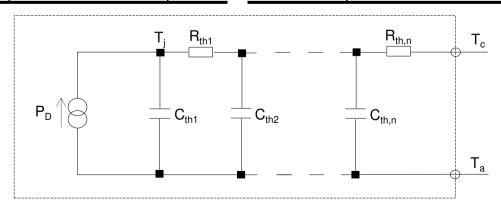
●Thermal resistance

Parameter	Symbol	Values			Unit
r didilielei		Min.	Тур.	Max.	
Thermal resistance, junction - case	$R_{thJC}^{}^{\star9}}$	-	0.65	0.85	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	4.9 ×10 ⁻²	
R _{th2}	3.0 ×10 ⁻¹	K/W
R _{th3}	3.0 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	8.7 ×10 ⁻⁴	
C_{th2}	4.0 ×10 ⁻³	Ws/K
C _{th3}	5.2 ×10 ⁻²	



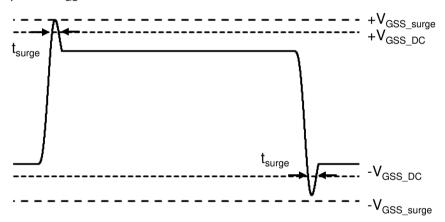
ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Davamatav	Cymahal	Symbol Conditions -	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g_{fs}^{*8}	$V_{DS} = 10V, I_{D} = 29A$	-	16	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	2320	-	
Output capacitance	C_{oss}	V _{DS} = 500V	ı	111	ı	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	ı	9	ı	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	ı	143	ı	pF
Total Gate charge	Q_g^{*8}	$V_{DS} = 500V$ $I_{D} = 29A$	ı	94	ı	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	ı	20	ı	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	23	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 500V$ $I_{D} = 29A$	ı	9.5	ı	
Rise time	t _r *8	$V_{GS} = +18V / 0V$	ı	22	ı	ns
Turn - off delay time	t _{d(off)} *8	$R_G = 6.8\Omega$, L = 250µH E_{on} includes diode	ı	45	ı	115
Fall time	t_f^{*8}	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	ı	13	ı	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	213	-	11.1
Turn - off switching loss	E _{off} *8		-	73	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vi} = 25°C unless otherwise specified)

Daramatar	Cumbal	Canditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_{S} = 29A$	ı	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 29A$ $V_B = 500V$	ı	12	Ī	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 2700A/µs	ı	141	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	ı	24	ı	Α

- *1 Limited by maximum T_{vj} and for Max. R_{thJC} .
- *2 Pulse width and duty cycle are limited by $T_{v_j,max}$.
- *3 Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%
- *4 When used as a protective function, PW \leq 10 μ s
- *5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that $V_{\text{GSS_surge}}$ must be in the range of absolute maximum rating.

- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

Fig.1 Power Dissipation Derating Curve

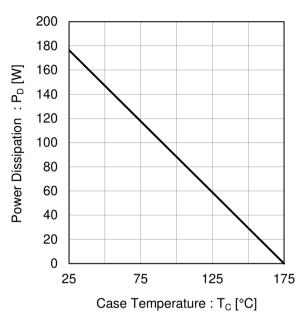


Fig.2 Maximum Safe Operating Area

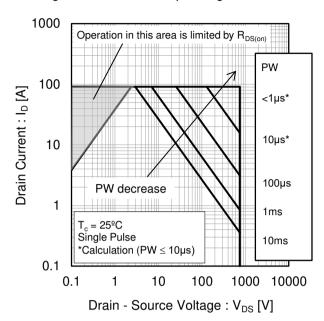
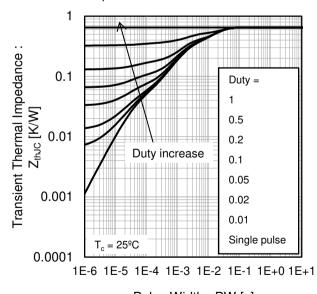
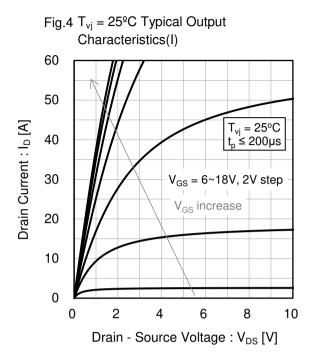


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



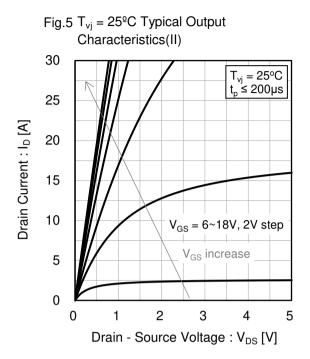
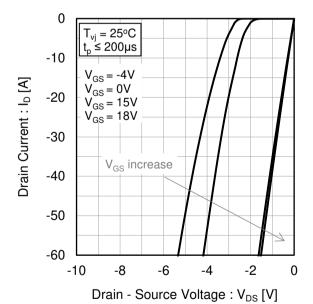
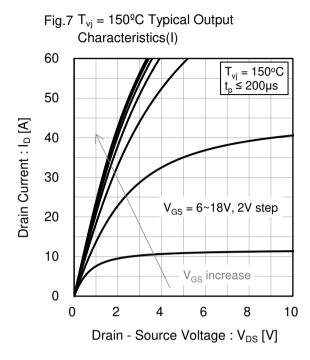
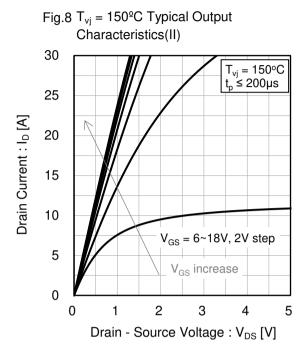
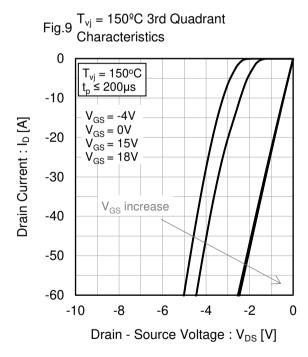


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics









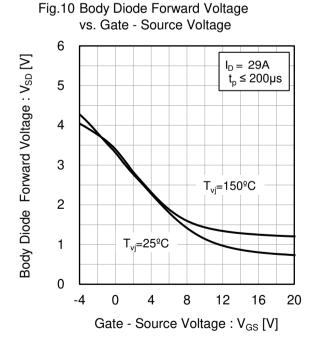


Fig.11 Typical Transfer Characteristics (I)

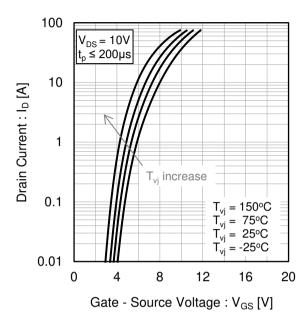


Fig.12 Typical Transfer Characteristics (II)

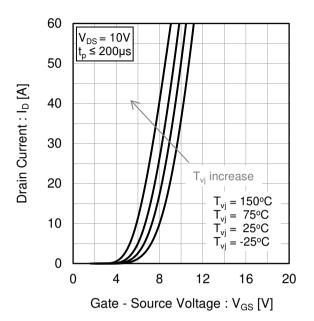


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

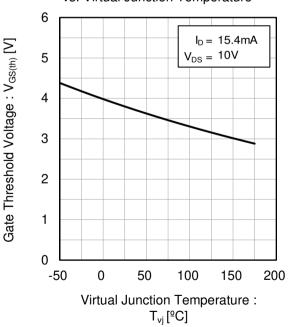
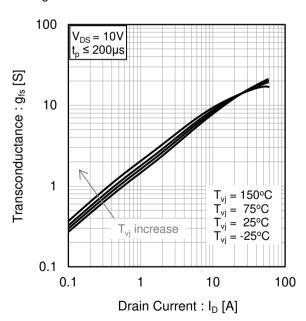
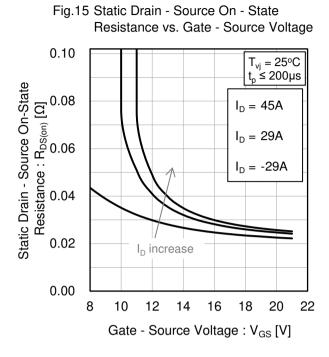


Fig.14 Transconductance vs. Drain Current



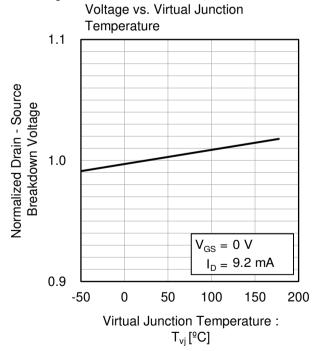


Resistance vs. Virtual Junction Temperature 0.10 $V_{GS} = 18V$ $t_p \le 200 \mu s$ = 45A = 29A $I_D = -29A$ I_D increase 0.00 -50 0 100 50 150 200 Virtual Junction Temperature: $T_{vi}[^{\circ}C]$

Fig.16 Static Drain - Source On - State

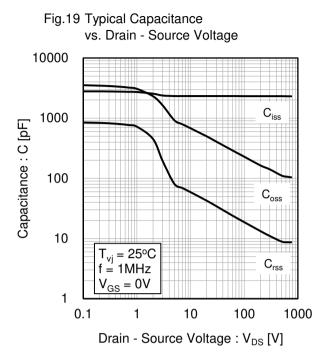
Resistance vs. Drain Current = 150°C = 125°C Static Drain - Source On-State 75°C = 25°C Resistance: $R_{DS(on)}[\Omega]$ -25°C 0.1 0.01 T_{vj} increase $V_{GS} = 18V$ $t_p \le 200 \mu s$ 0.001 10 100 Drain Current: I_D [A]

Fig.17 Static Drain - Source On - State



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Fig.18 Normalized Drain - Source Breakdown



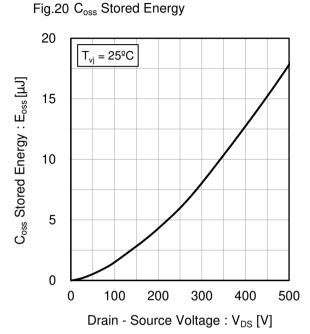


Fig.21 Dynamic Input Characteristics

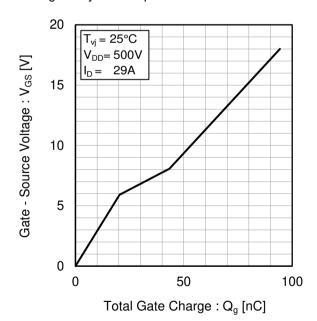


Fig.22 Typical Switching Time vs. External Gate Resistance 125 25°C $I_D =$ 29A V_{DD}= 500V 100 $V_{GS} = +18V/0V$ $t_{\text{d(off)}} \\$ Switching Time:t[ns] $L = 250 \mu H$ 75 50 25 $t_{\rm f}$ 0

5

0

vs. Drain - Source Voltage

600 $T_{vj} = 25^{\circ}C$ $I_{D} = 29A$ $V_{GS} = +18V/0V$ $R_{G} = 6.8\Omega$ $L = 250\mu H$ 300

200 E_{on}

Fig.23 Typical Switching Loss

Switching Loss: E [µJ]

100

0

External Gate Resistance : $R_G[\Omega]$

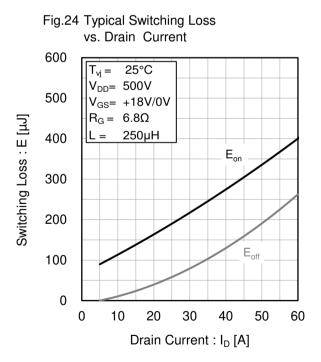
10

15

20

100 200 300 400 500

Drain - Source Voltage : V_{DS} [V]



vs. External Gate Resistance 600 $T_{vj} = 25^{\circ}C$ $I_D = 29A$ 500 $V_{DD} = 500V$ E_{on} $V_{GS} = +18V/0V$ Switching Loss: E [µJ] $L = 250 \mu H$ 400 300 $\mathsf{E}_{\mathsf{off}}$ 200 100 0 5 0 10 15 20 External Gate Resistance : $R_G[\Omega]$

Fig.25 Typical Switching Loss

• Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

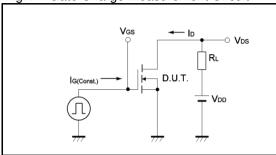


Fig.2-1 Switching Characteristics Measurement Circuit

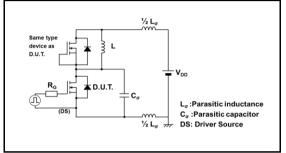


Fig.2-3 Waveforms for Switching Energy Loss

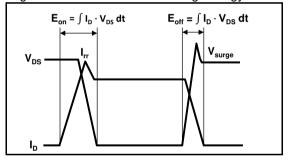


Fig.3-1 Reverse Recovery Time Measurement Circuit

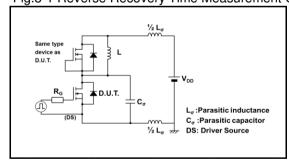


Fig.1-2 Gate Charge Waveform

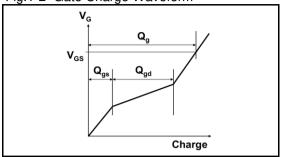


Fig.2-2 Waveforms for Switching Time

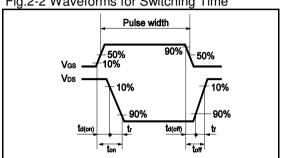
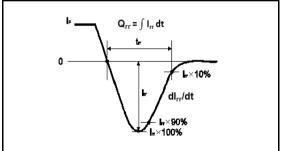
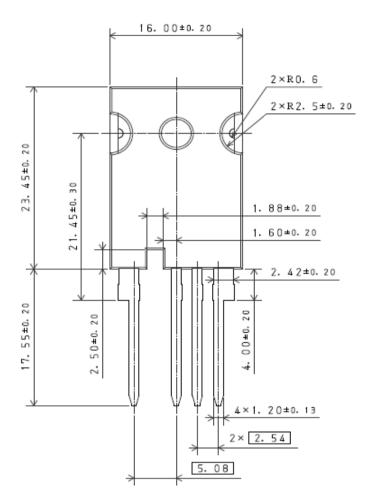
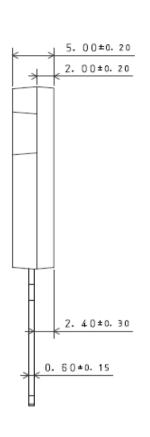


Fig.3-2 Reverse Recovery Waveform

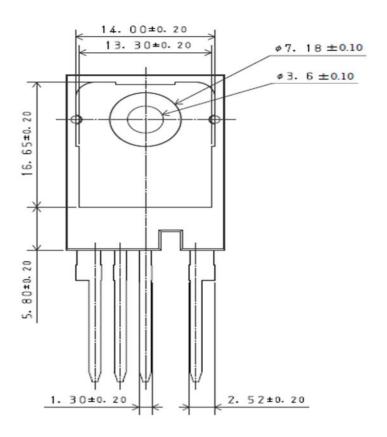


Package Dimensions



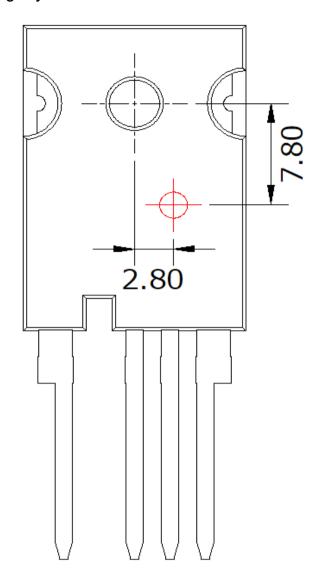


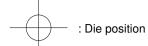
Unit: mm



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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